#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ T <sub>L</sub> = 25°C, Pulse Width = 1 ms	P <sub>PK</sub>	400	W
DC Power Dissipation @ T <sub>L</sub> = 75°C Measured Zero Lead Length (Note 2)	P <sub>D</sub>	1.5	W
Derate Above 75°C		20	mW/°C
Thermal Resistance from Junction to Lead	$R_{ heta JL}$	50	°C/W
DC Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C Derate Above 25°C	$P_{D}$	0.5 4.0	W mW/°C
Thermal Resistance from Junction to Ambient	$R_{ heta JA}$	250	°C/W
Forward Surge Current (Note 4) @ T <sub>A</sub> = 25°C	I <sub>FSM</sub>	40	Α
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

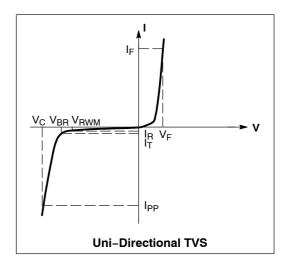
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. 10 X 1000 μs, non–repetitive.
- 2. 1" square copper pad, FR-4 board.
- 3. FR-4 board, using ON Semiconductor minimum recommended footprint, as shown in 403B case outline dimensions spec.
- 4. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

# **ELECTRICAL CHARACTERISTICS** ( $T_A$ = 25°C unless otherwise noted, $V_F$ = 3.5 V Max. @ $I_F$ = 30 A for all types) (Note 5)

Symbol	Parameter					
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current					
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>					
V <sub>RWM</sub>	Working Peak Reverse Voltage					
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>					
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>					
I <sub>T</sub>	Test Current					
IF	Forward Current					
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>					

5. 1/2 sine wave or equivalent, PW = 8.3 ms, non-repetitive duty cycle.



### **ELECTRICAL CHARACTERISTICS**

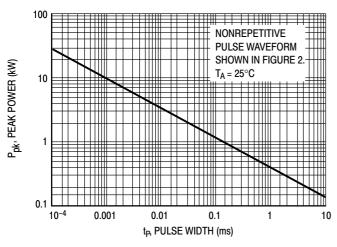
		V <sub>RWM</sub> (Note 6)	I <sub>R</sub> @ V <sub>RWM</sub>	Breakdown Voltage			V <sub>C</sub> @ I <sub>PP</sub> (Note 8)		C Typ.	
	Device			V <sub>BR</sub> (Volts) (Note 7) @ I <sub>T</sub>			@ I <sub>T</sub>	V <sub>C</sub> I <sub>PP</sub>		(Note 9)
Device	Marking	Volts	μ <b>Α</b>	Min	Nom	Max	mA	Volts	Amps	pF
1SMA5.0AT3, G	QE	5.0	400	6.4	6.7	7.0	10	9.2	43.5	2035
1SMA6.0AT3, G	QG	6.0	400	6.67	7.02	7.37	10	10.3	38.8	1730
1SMA6.5AT3, G	QK	6.5	250	7.22	7.6	7.98	10	11.2	35.7	1605
1SMA7.0AT3, G	QM	7.0	250	7.78	8.19	8.6	10	12.0	33.3	1505
1SMA7.5AT3, G	QP	7.5	50	8.33	8.77	9.21	1	12.9	31.0	1415
1SMA8.0AT3, G	QR	8.0	25	8.89	9.36	9.83	1	13.6	29.4	1035
1SMA8.5AT3, G	QT	8.5	5.0	9.44	9.92	10.4	1	14.4	27.8	1265
1SMA9.0AT3, G	QV	9.0	2.5	10	10.55	11.1	1	15.4	26.0	1200
1SMA10AT3, G	QX	10	2.5	11.1	11.7	12.3	1	17.0	23.5	1090
1SMA11AT3, G	QZ	11	2.5	12.2	12.85	13.5	1	18.2	22.0	1000
1SMA12AT3, G	RE	12	2.5	13.3	14.0	14.7	1	19.9	20.1	925
1SMA13AT3, G	RG	13	2.5	14.4	15.15	15.9	1	21.5	18.6	860
1SMA15AT3, G	RM	15	2.5	16.7	17.6	18.5	1	24.4	16.4	758
1SMA16AT3, G	RP	16	2.5	17.8	18.75	19.7	1	26.0	15.4	715
1SMA17AT3, G	RR	17	2.5	18.9	19.9	20.9	1	27.6	14.5	680
1SMA18AT3, G	RT	18	2.5	20	21.05	22.1	1	29.2	13.7	645
1SMA20AT3, G	RV	20	2.5	22.2	23.35	24.5	1	32.4	12.3	585
1SMA22AT3, G	RX	22	2.5	24.4	25.65	26.9	1	35.5	11.3	540
1SMA24AT3, G	RZ	24	2.5	26.7	28.1	29.5	1	38.9	10.3	500
1SMA26AT3, G	SE	26	2.5	28.9	30.4	31.9	1	42.1	9.5	460
1SMA28AT3, G	SG	28	2.5	31.1	32.75	34.4	1	45.4	8.8	430
1SMA30AT3, G	SK	30	2.5	33.3	35.05	36.8	1	48.4	8.3	405
1SMA33AT3, G	SM	33	2.5	36.7	38.65	40.6	1	53.3	7.5	375
1SMA36AT3, G	SP	36	2.5	40	42.1	44.2	1	58.1	6.9	345
1SMA40AT3, G	SR	40	2.5	44.4	46.75	49.1	1	64.5	6.2	315
1SMA43AT3, G	ST	43	2.5	47.8	50.3	52.8	1	69.4	5.8	295
1SMA45AT3, G	SV	45	2.5	50	52.65	55.3	1	72.2	5.5	280
1SMA48AT3, G	SX	48	2.5	53.3	56.1	58.9	1	77.4	5.2	265
1SMA51AT3, G	SZ	51	2.5	56.7	59.7	62.7	1	82.4	4.9	250
1SMA54AT3, G	TE	54	2.5	60	63.15	66.3	1	87.1	4.6	240
1SMA58AT3, G	TG	58	2.5	64.4	67.8	71.5	1	93.6	4.3	225
1SMA64AT3, G	TM	64	2.5	71.1	74.85	78.6	1	103	3.9	205
1SMA70AT3, G	TP	70	2.5	77.8	81.9	86.0	1	113	3.5	190
1SMA75AT3, G	TR	75	2.5	83.3	87.7	92.1	1	121	3.3	180

A transient suppressor is normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal to or greater than the DC or continuous peak operating voltage level.
 V<sub>BR</sub> measured at pulse test current I<sub>T</sub> at an ambient temperature of 25°C.
 Surge current waveform per Figure 2 and derate per Figure 3.
 Bias voltage = 0 V, F = 1.0 MHz, T<sub>J</sub> = 25°C.

<sup>†</sup>Please see 1SMA10CAT3 to 1SMA75CAT3 for Bidirectional devices.

<sup>\*</sup>The "G" suffix indicates Pb-Free package available.

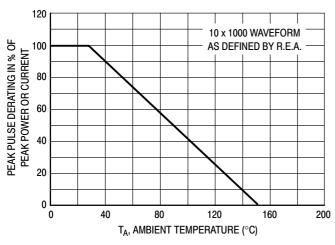
#### RATING AND TYPICAL CHARACTERISTIC CURVES



120 T<sub>A</sub> = 25°C ≤ 10 μs PW (ID) IS DEFINED AS THE lppm, PEAK PULSE CURRENT (%) 100 POINT WHERE THE PEAK CURRENT DECAYS TO 50% OF Ipp. PEAK VALUE -80 Ippm 60 HALF VALUE - Ipp/2 40 10/1000 μs WAVEFORM AS DEFINED BY R.E.A. 20 0 0 2 3 t, TIME (ms)

Figure 1. Pulse Rating Curve

Figure 2. Pulse Waveform



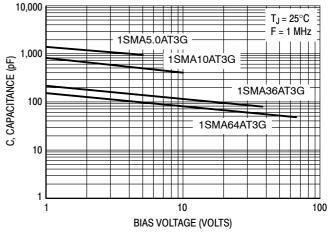


Figure 3. Pulse Derating Curve

Figure 4. Typical Junction Capacitance vs.
Bias Voltage

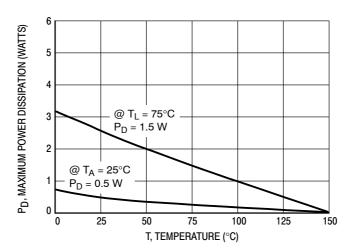
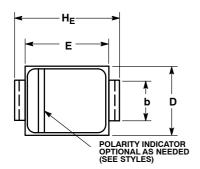


Figure 5. Steady State Power Derating

#### PACKAGE DIMENSIONS

## **SMA**

CASE 403D-02 ISSUE F



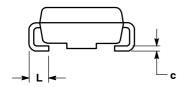
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- 403D-01 OBSOLETE, NEW STANDARD IS 403D-02.

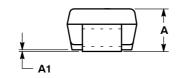
	M	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.97	2.10	2.20	0.078	0.083	0.087	
A1	0.05	0.10	0.15	0.002	0.004	0.006	
b	1.27	1.45	1.63	0.050	0.057	0.064	
С	0.15	0.28	0.41	0.006	0.011	0.016	
D	2.29	2.60	2.92	0.090	0.103	0.115	
E	4.06	4.32	4.57	0.160	0.170	0.180	
HE	4.83	5.21	5.59	0.190	0.205	0.220	
L	0.76	1.14	1.52	0.030	0.045	0.060	



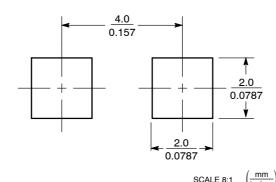
PIN 1. CATHODE (POLARITY BAND)

2. ANODE





#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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